

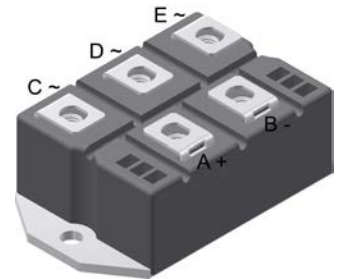
Standard Rectifier Module

3~ Rectifier
$V_{RRM} = 1200\text{ V}$
$I_{DAV} = 125\text{ A}$
$I_{FSM} = 1200\text{ A}$

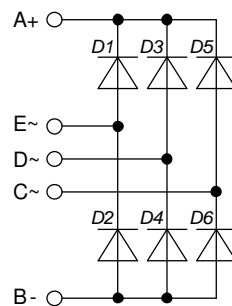
3~ Rectifier Bridge

Part number

VUO110-12N07



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-E

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

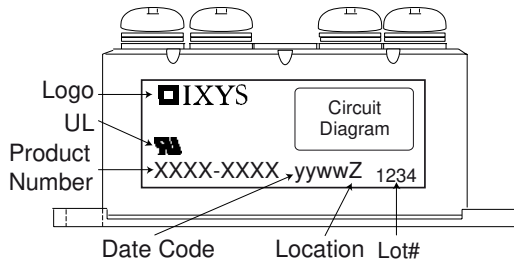
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1300	V
V_{RRM}	max. repetitive reverse blocking voltage					1200	V
I_R	reverse current	$V_R = 1200\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		100	μA
		$V_R = 1200\text{ V}$		$T_{VJ} = 150^\circ\text{C}$		2	mA
V_F	forward voltage drop	$I_F = 50\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		1,13	V
		$I_F = 150\text{ A}$				1,46	V
		$I_F = 50\text{ A}$		$T_{VJ} = 125^\circ\text{C}$		1,04	V
		$I_F = 150\text{ A}$				1,47	V
I_{DAV}	bridge output current	$T_C = 110^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		125	A
		rectangular	$d = \frac{1}{3}$				
V_{FO}	threshold voltage			$T_{VJ} = 150^\circ\text{C}$		0,79	V
r_F	slope resistance					4,5	m Ω
						} for power loss calculation only	
R_{thJC}	thermal resistance junction to case					0,7	K/W
R_{thCH}	thermal resistance case to heatsink				0,3		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		175	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 45^\circ\text{C}$		1,20	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		1,30	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 150^\circ\text{C}$		1,02	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		1,10	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 45^\circ\text{C}$		7,20	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		6,98	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 150^\circ\text{C}$		5,20	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		5,04	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$		37	pF



Package PWS-E				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I_{RMS}	RMS current	per terminal			200	A	
T_{VJ}	virtual junction temperature		-40		150	°C	
T_{op}	operation temperature		-40		125	°C	
T_{stg}	storage temperature		-40		125	°C	
Weight					284	g	
M_D	mounting torque		4,25		5,75	Nm	
M_T	terminal torque		4,25		5,75	Nm	
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	12,0			mm	
$d_{Spb/Apb}$		terminal to backside	26,0			mm	
V_{ISOL}	isolation voltage	t = 1 second	3000			V	
		t = 1 minute	2500			V	

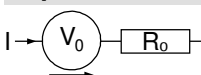


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO110-12NO7	VUO110-12NO7	Box	5	462373

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$

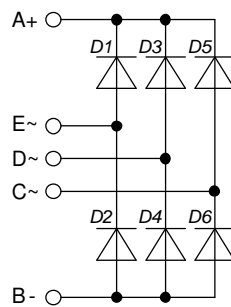
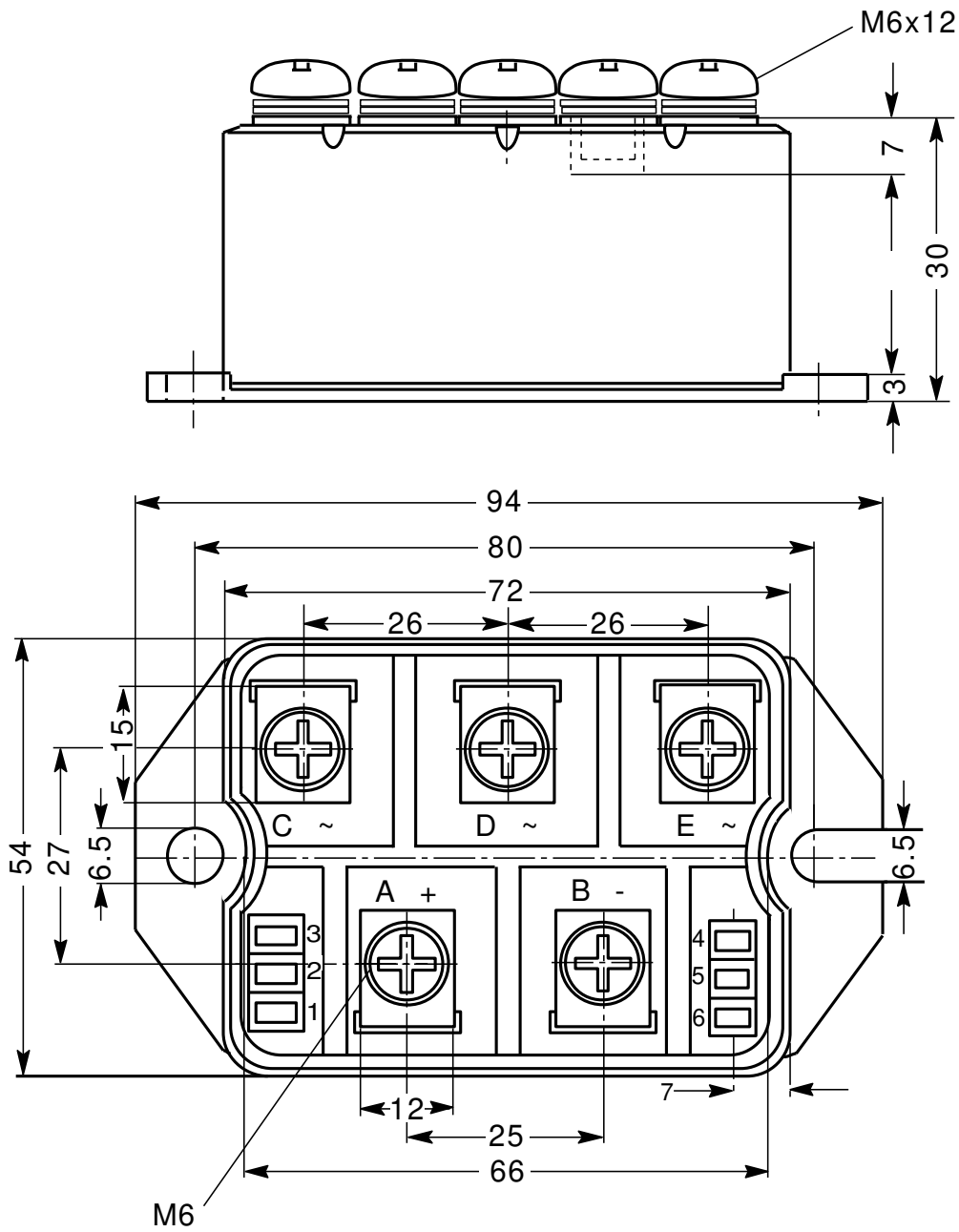


Rectifier

$V_{0\ max}$	threshold voltage	0,79	V
$R_{0\ max}$	slope resistance *	3,3	mΩ



Outlines PWS-E





Rectifier

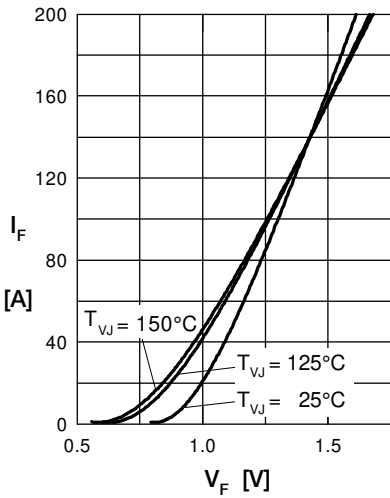


Fig. 1 Forward current vs. voltage drop per diode

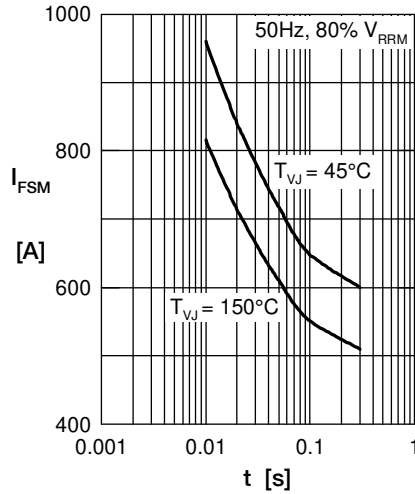


Fig. 2 Surge overload current vs. time per diode

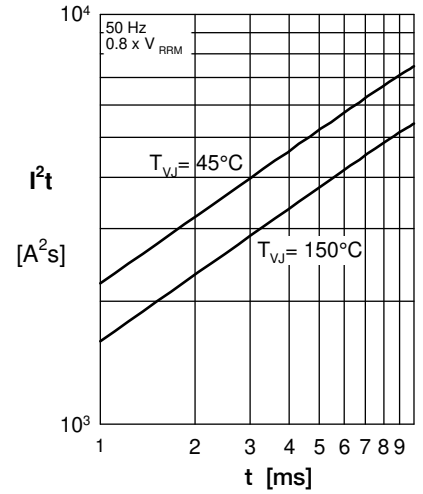


Fig. 3 I^2t vs. time per diode

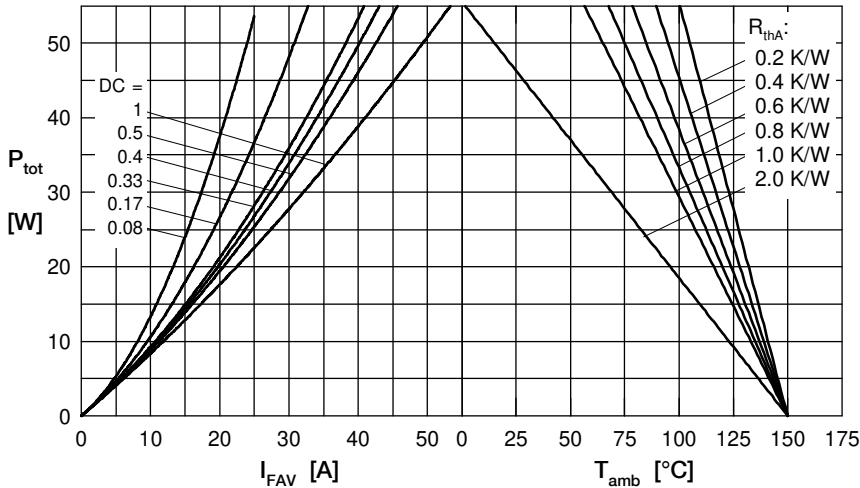


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

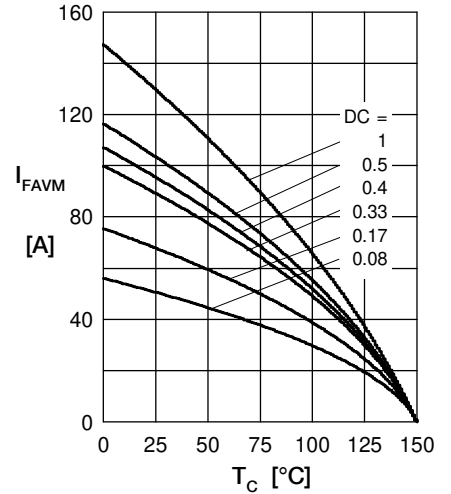


Fig. 5 Max. forward current vs. case temperature per diode

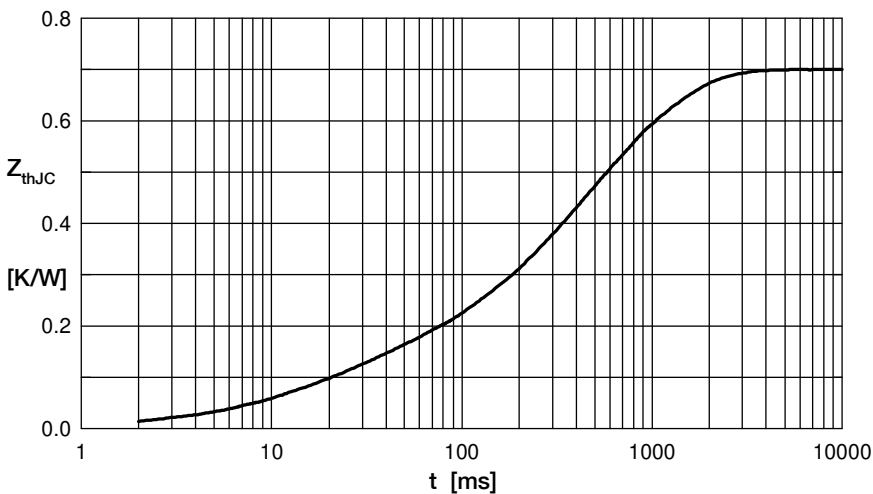


Fig. 6 Transient thermal impedance junction to case vs. time per diode

R_i	t_i
0.100	0.020
0.010	0.010
0.162	0.225
0.258	0.800
0.170	0.580